

Polar™ Power MOSFETs

HiPerFET™

IXFV52N30P
IXFV52N30PS
IXFH52N30P

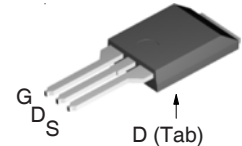
N-Channel Enhancement Mode
 Avalanche Rated
 Fast Intrinsic Diode



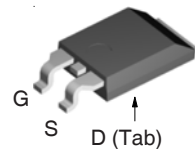
$V_{DSS} = 300V$
 $I_{D25} = 52A$
 $R_{DS(on)} \leq 73m\Omega$
 $t_{rr} \leq 200ns$

| Symbol | Test Conditions | Maximum Ratings | |
|---------------|--|------------------|------------|
| V_{DSS} | $T_J = 25^\circ C$ to $150^\circ C$ | 300 | V |
| V_{DGR} | $T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1M\Omega$ | 300 | V |
| V_{GSS} | Continuous | ± 20 | V |
| V_{GSM} | Transient | ± 30 | V |
| I_{D25} | $T_C = 25^\circ C$ | 52 | A |
| I_{DM} | $T_C = 25^\circ C$, Pulse Width Limited by T_{JM} | 150 | A |
| I_A | $T_C = 25^\circ C$ | 52 | A |
| E_{AS} | $T_C = 25^\circ C$ | 1 | J |
| dv/dt | $I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ C$ | 10 | V/ns |
| P_D | $T_C = 25^\circ C$ | 400 | W |
| T_J | | -55 ... +150 | $^\circ C$ |
| T_{JM} | | 150 | $^\circ C$ |
| T_{stg} | | -55 ... +150 | $^\circ C$ |
| T_L | Maximum Lead Temperature for Soldering | 300 | $^\circ C$ |
| T_{SOLD} | Plastic Body for 10s | 260 | $^\circ C$ |
| M_d | Mounting Torque (TO-247) | 1.13/10 | Nm/lb.in |
| F_C | Mounting Force (PLUS220) | 11..65/2.5..14.6 | N/lb |
| Weight | PLUS220 & PLUS220SMD | 4 | g |
| | TO-247 | 6 | g |

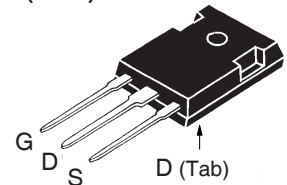
PLUS220 (IXFV)



PLUS220SMD (IXFV_S)



TO-247 (IXFH)



G = Gate D = Drain
 S = Source Tab = Drain

Features

- Fast Intrinsic Rectifier
- Avalanche Rated
- Low $R_{DS(ON)}$ and Q_G
- Low Package Inductance

Advantages

- High Power Density
- Easy to Mount
- Space Savings

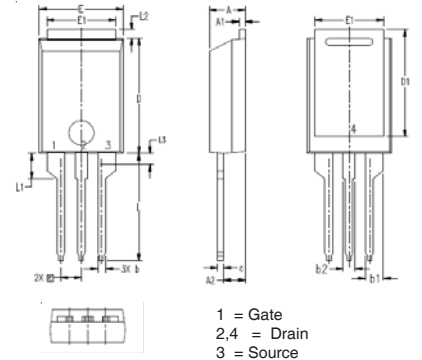
Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- Laser Drivers
- AC and DC Motor Drives
- Robotics and Servo Controls

| Symbol | Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified) | Characteristic Values | | |
|--------------|---|-----------------------|------|--------------------|
| | | Min. | Typ. | Max. |
| BV_{DSS} | $V_{GS} = 0V$, $I_D = 250\mu A$ | 300 | | V |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 4mA$ | 2.5 | | 5.0 V |
| I_{GSS} | $V_{GS} = \pm 20V$, $V_{DS} = 0V$ | | | ± 100 nA |
| I_{DSS} | $V_{DS} = V_{DSS}$, $V_{GS} = 0V$ $T_J = 125^\circ C$ | | | 25 μA 1 mA |
| $R_{DS(on)}$ | $V_{GS} = 10V$, $I_D = 0.5 \cdot I_{D25}$, Note 1 | | | 73 m Ω |

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified) | Characteristic Values | | |
|--------------|---|-----------------------|------|-------------------------|
| | | Min. | Typ. | Max. |
| g_{fs} | $V_{DS} = 10\text{V}, I_D = 0.5 \cdot I_{D25}$, Note 1 | 20 | 30 | S |
| C_{iss} | $V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$ | | 3490 | pF |
| C_{oss} | | | 550 | pF |
| C_{rss} | | | 130 | pF |
| $t_{d(on)}$ | Resistive Switching Times $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 52\text{A}$ $R_G = 4\Omega$ (External) | | 24 | ns |
| t_r | | | 22 | ns |
| $t_{d(off)}$ | | | 60 | ns |
| t_f | | | 20 | ns |
| $Q_{g(on)}$ | $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ | | 110 | nC |
| Q_{gs} | | | 25 | nC |
| Q_{gd} | | | 53 | nC |
| R_{thJC} | | | | 0.31 $^\circ\text{C/W}$ |
| R_{thCS} | (TO-247 & PLUS220) | 0.25 | | $^\circ\text{C/W}$ |

PLUS220 (IXFV) Outline



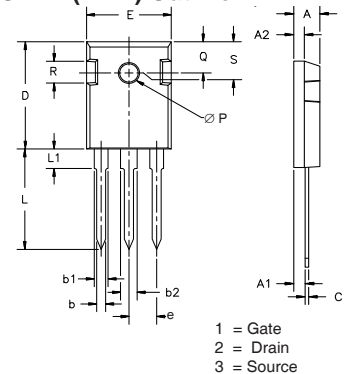
| SYM | INCHES | | MILLIMETER | |
|-----|----------|------|------------|-------|
| | MIN | MAX | MIN | MAX |
| A | .169 | .185 | 4.30 | 4.70 |
| A1 | .028 | .035 | 0.70 | 0.90 |
| A2 | .098 | .118 | 2.50 | 3.00 |
| b | .035 | .047 | 0.90 | 1.20 |
| b1 | .080 | .095 | 2.03 | 2.41 |
| b2 | .054 | .064 | 1.37 | 1.63 |
| c | .028 | .035 | 0.70 | 0.90 |
| D | .551 | .591 | 14.00 | 15.00 |
| D1 | .512 | .539 | 13.00 | 13.70 |
| E | .394 | .433 | 10.00 | 11.00 |
| E1 | .331 | .346 | 8.40 | 8.80 |
| e | .100 BSC | | 2.54 BSC | |
| L | .512 | .551 | 13.00 | 14.00 |
| L1 | .118 | .138 | 3.00 | 3.50 |
| L2 | .035 | .051 | 0.90 | 1.30 |
| L3 | .047 | .059 | 1.20 | 1.50 |

Source-Drain Diode

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified) | Characteristic Values | | |
|----------|---|-----------------------|------|--------|
| | | Min. | Typ. | Max. |
| I_S | $V_{GS} = 0\text{V}$ | | | 52 A |
| I_{SM} | Repetitive, pulse width limited by T_{JM} | | | 150 A |
| V_{SD} | $I_F = I_S, V_{GS} = 0\text{V}$, Note 1 | | | 1.5 V |
| t_{rr} | $I_F = 25\text{A}, -di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}, V_{GS} = 0\text{V}$ | | 160 | 200 ns |
| Q_{RM} | | | 800 | nC |
| I_{RM} | | | 7 | A |

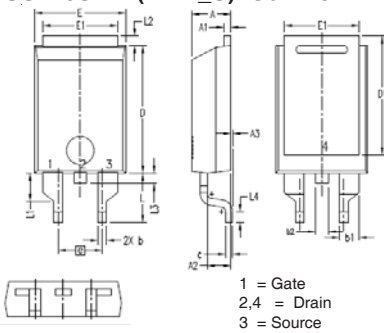
Note 1: Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

TO-247 (IXFH) Outline



| Dim. | Millimeter | | Inches | |
|----------------|------------|-------|--------|-------|
| | Min. | Max. | Min. | Max. |
| A | 4.7 | 5.3 | .185 | .209 |
| A ₁ | 2.2 | 2.54 | .087 | .102 |
| A ₂ | 2.2 | 2.6 | .059 | .098 |
| b | 1.0 | 1.4 | .040 | .055 |
| b ₁ | 1.65 | 2.13 | .065 | .084 |
| b ₂ | 2.87 | 3.12 | .113 | .123 |
| C | .4 | .8 | .016 | .031 |
| D | 20.80 | 21.46 | .819 | .845 |
| E | 15.75 | 16.26 | .610 | .640 |
| e | 5.20 | 5.72 | 0.205 | 0.225 |
| L | 19.81 | 20.32 | .780 | .800 |
| L1 | | 4.50 | | .177 |
| ∅P | 3.55 | 3.65 | .140 | .144 |
| Q | 5.89 | 6.40 | 0.232 | 0.252 |
| R | 4.32 | 5.49 | .170 | .216 |
| S | 6.15 | BSC | 242 | BSC |

PLUS220SMD (IXFV_S) Outline



| SYM | INCHES | | MILLIMETER | |
|-----|----------|------|------------|-------|
| | MIN | MAX | MIN | MAX |
| A | .169 | .185 | 4.30 | 4.70 |
| A1 | .028 | .035 | 0.70 | 0.90 |
| A2 | .098 | .118 | 2.50 | 3.00 |
| A3 | .000 | .010 | 0.00 | 0.25 |
| b | .035 | .047 | 0.90 | 1.20 |
| b1 | .080 | .095 | 2.03 | 2.41 |
| b2 | .054 | .064 | 1.37 | 1.63 |
| c | .028 | .035 | 0.70 | 0.90 |
| D | .551 | .591 | 14.00 | 15.00 |
| D1 | .512 | .539 | 13.00 | 13.70 |
| E | .394 | .433 | 10.00 | 11.00 |
| E1 | .331 | .346 | 8.40 | 8.80 |
| e | .200 BSC | | 5.08 BSC | |
| L | .209 | .228 | 5.30 | 5.80 |
| L1 | .118 | .138 | 3.00 | 3.50 |
| L2 | .035 | .051 | 0.90 | 1.30 |
| L3 | .047 | .059 | 1.20 | 1.50 |
| L4 | .039 | .059 | 1.00 | 1.50 |

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

| | | | | | | | | | | |
|--|-----------|-----------|-----------|-----------|--------------|--------------|--------------|--------------|--------------|--------------|
| IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: | 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665 | 6,404,065 B1 | 6,683,344 | 6,727,585 | 7,005,734 B2 | 7,157,338 B2 |
| | 4,860,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123 B1 | 6,534,343 | 6,710,405 B2 | 6,759,692 | 7,063,975 B2 | |
| | 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728 B1 | 6,583,505 | 6,710,463 | 6,771,478 B2 | 7,071,537 | |

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

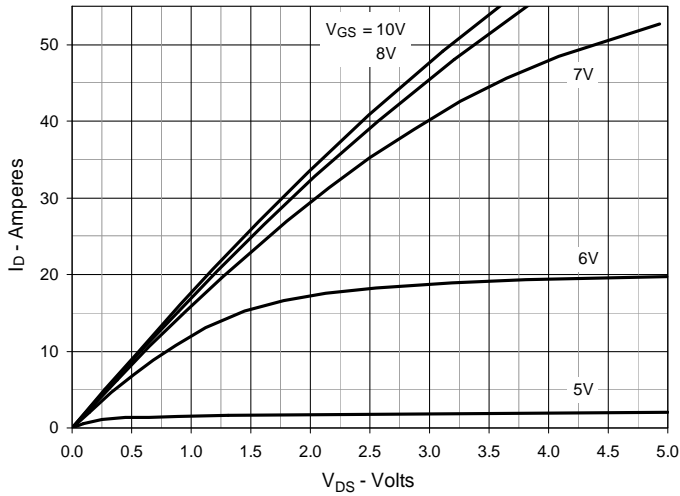


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

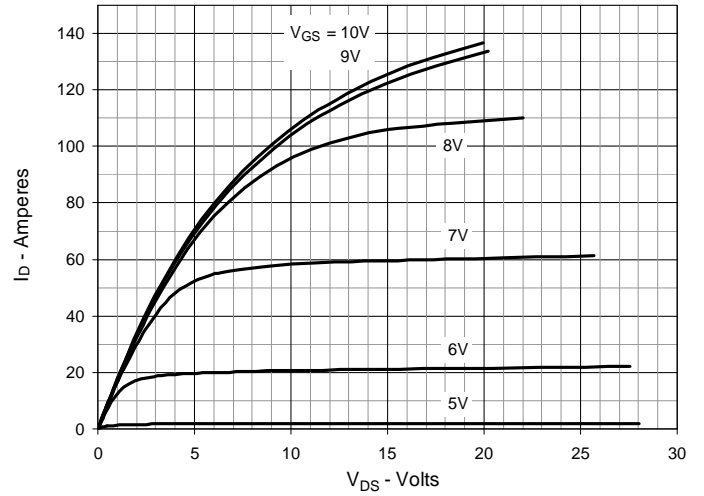


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

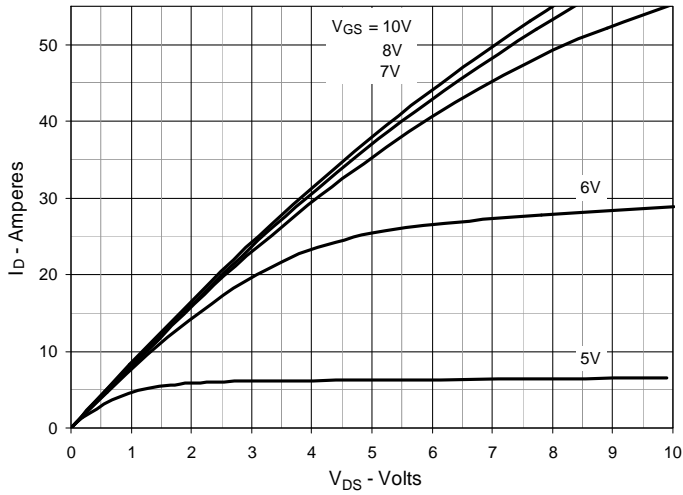


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 26\text{A}$ Value vs. Junction Temperature

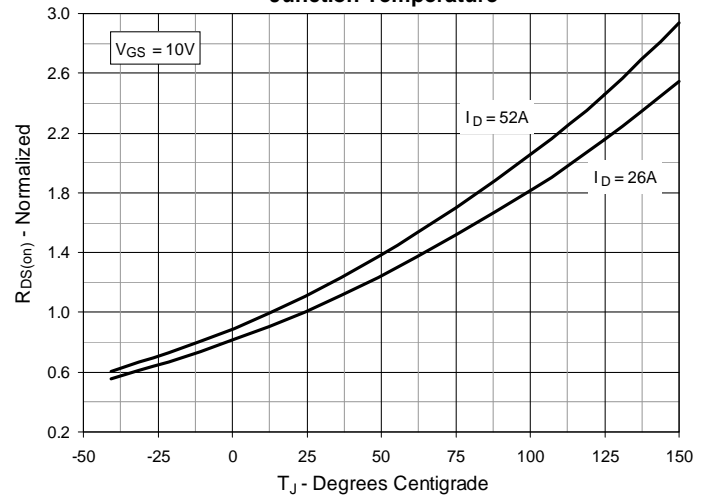


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 26\text{A}$ Value vs. Drain Current

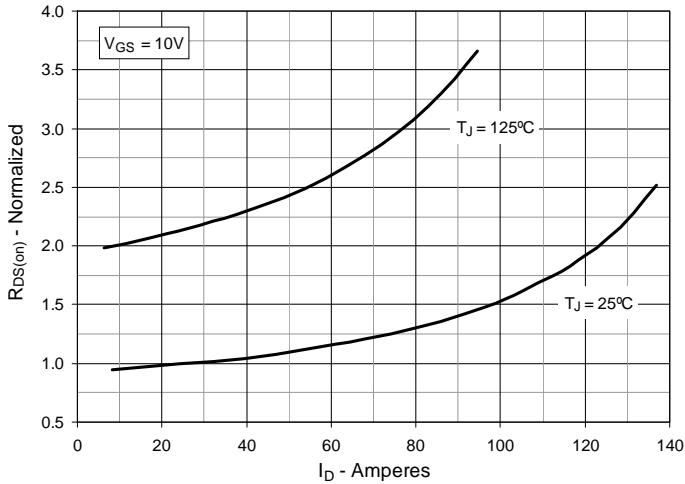


Fig. 6. Maximum Drain Current vs. Case Temperature

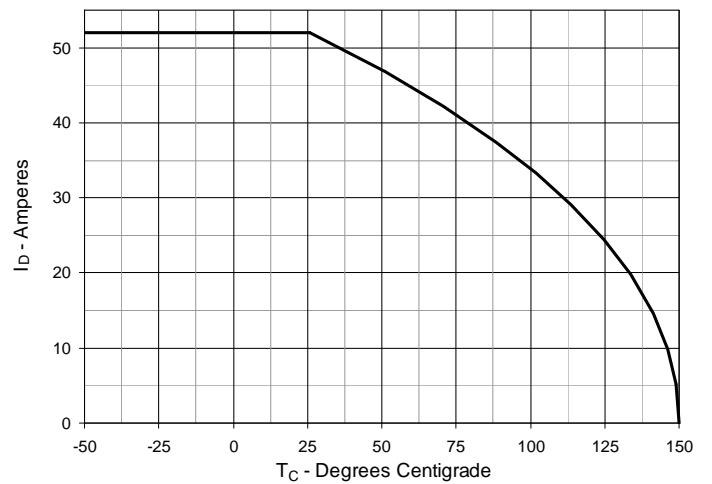


Fig. 7. Input Admittance

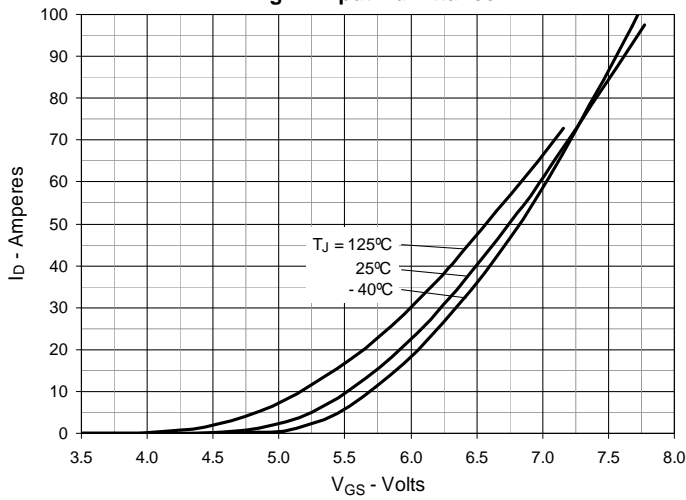


Fig. 8. Transconductance

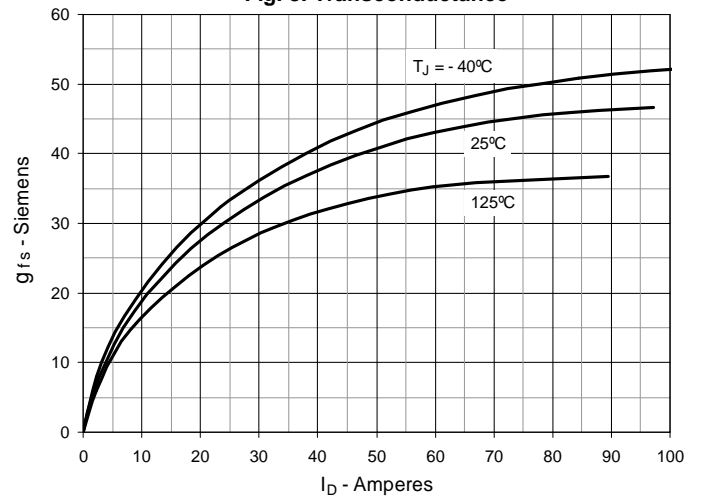


Fig. 9. Forward Voltage Drop of Intrinsic Diode

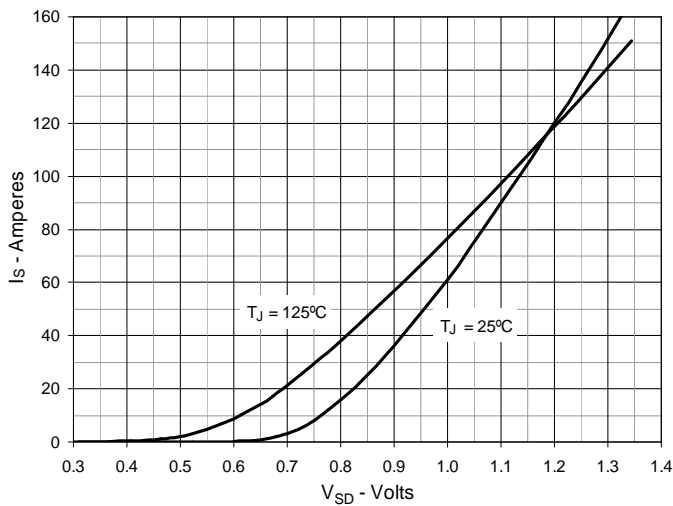


Fig. 10. Gate Charge

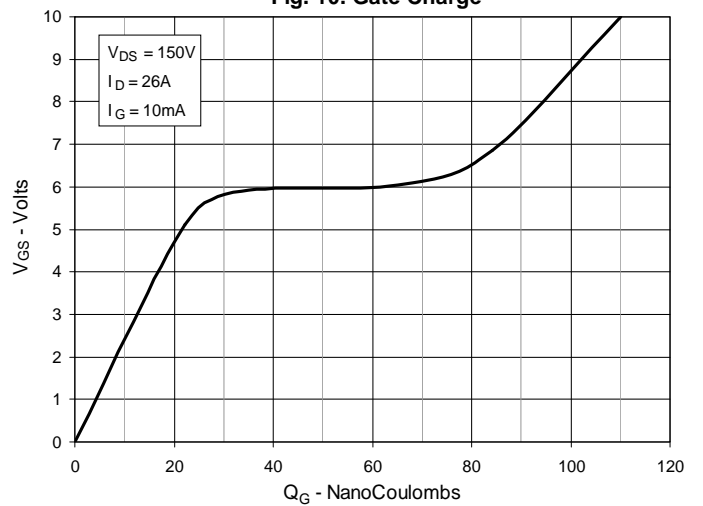


Fig. 11. Capacitance

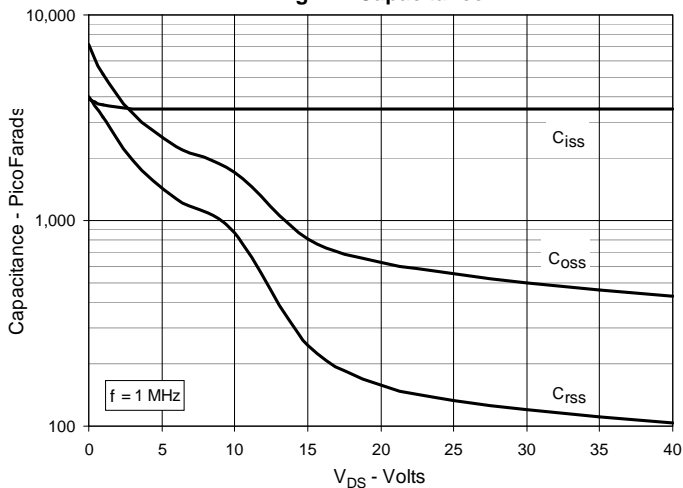


Fig. 12. Forward-Bias Safe Operating Area

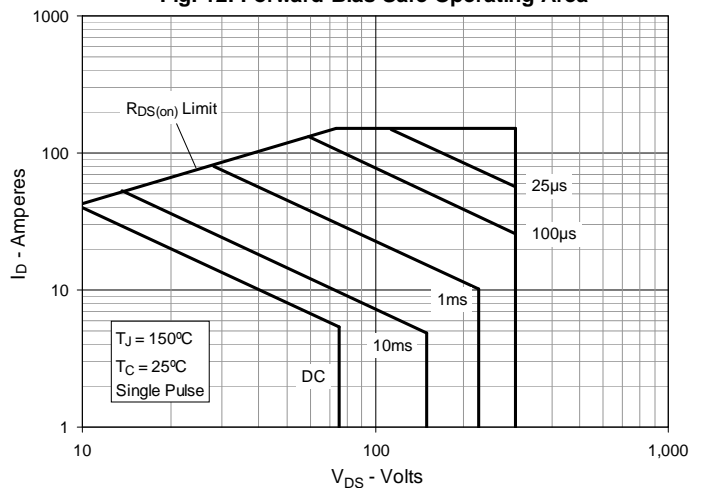


Fig. 13. Maximum Transient Thermal Impedance

